

Abstract

The invention relates to a method for production of a metallic or metal-containing layer (5) by using a precursor on a silicon- or germanium-containing layer, of, in particular, an electronic component, whereby an intermediate layer is applied to the silicon- or germanium-containing layer before the use of the precursor. Said intermediate layer forms a diffusion barrier for at least those elements or the pre-cursor which would etch the silicon- or germanium-containing layer and is itself resistant to etching by the precursor